

THE EFFECT OF UNIAXIAL STRESS ON THE OFF-CENTER POTENTIAL  
OF  $\text{Cu}^+$  AND  $\text{Ag}^+$  DEFECTS IN ALKALI HALIDE CRYSTALS

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Odd parity lattice distortions near  $\text{Cu}^+$  and  $\text{Ag}^+$  defect ions on normal lattice sites in alkali halide crystals mix electronic defect states of different parity and give rise to a noticeable oscillator strength of the parity-forbidden electric dipole transitions  $n d^0 \rightarrow n d^1$  ( $n = 3$  for  $\text{Cu}^+$ ,  $n = 4$  for  $\text{Ag}^+$ ) in the UV-spectral range. In this way the intensity of the absorption bands indicates the behaviour of the local lattice distortions under extraneous fields or at different temperatures and enables us to study the potential of the defect ion. Here we report on the effect of uniaxial stress on the potential of  $\text{Cu}^+$  in KCl and  $\text{Ag}^+$  in rubidium halides, where the small defect ion shifts from the symmetry center of the lattice cell to an off-centre position.

For sufficiently large off-center distortions the defect potential can be approximated by a number of separated and symmetrically arranged potential wells with high walls between them (1). We describe the defect displacement from the symmetry center by the symmetry coordinate  $\vec{Q}_4$  which transforms as a vector under the elements of the point group  $O_h$ . The relevant odd-parity term of the electron-lattice interaction for the defect ion in the  $n$ -th potential well is given by:

$$H'_{el} = \sum_{i=1}^3 V_{4i} \{ Q_{4in}^- + Q_{4i}^- \} \quad [1]$$

where  $\vec{Q}_{4n}$  is the static displacement of the defect ion and  $\vec{Q}_{4n}$  describes vibrational distortions of the symmetry  $\Gamma_4^-$ . For the oscillator strength of a parity forbidden electric dipole transition from the ground state  $|j^+\rangle$  to the excited state  $|k^+\rangle$  we obtain by using perturbation theory:

$$f_{j \rightarrow k} = \sum_n \frac{e^{-\frac{E_n}{kT}}}{\sum_n e^{-\frac{E_n}{kT}}} \cdot \sum_{l,m=1}^3 B_{lm}(j,k) (\langle \vec{Q}_{4l} | \vec{Q}_{4l} | \vec{Q}_{4m} \rangle + \langle \vec{Q}_{4l} | \vec{Q}_{4m} \rangle ) \quad [2]$$

The Boltzmann-factor considers the occupation probability of the  $n$ -th potential well with minimum energy  $E_n$ . The first term of [2] is due to static off-center distortions, the second term describes the component of the oscillator strength which is due to vibrations.  $\langle \rangle$  means the thermal average.

Uniaxial stress affects the oscillator strength [2] in three different ways: First the off-center elongation  $\vec{Q}_{4n}$  of the defect ion in the stressed crystal depends on the projection of  $\vec{Q}_{4n}$  on the stress axis, and secondly the frequency  $\omega$  of the "odd" mode in a single well may split (1), (2). Here we report on the change of the

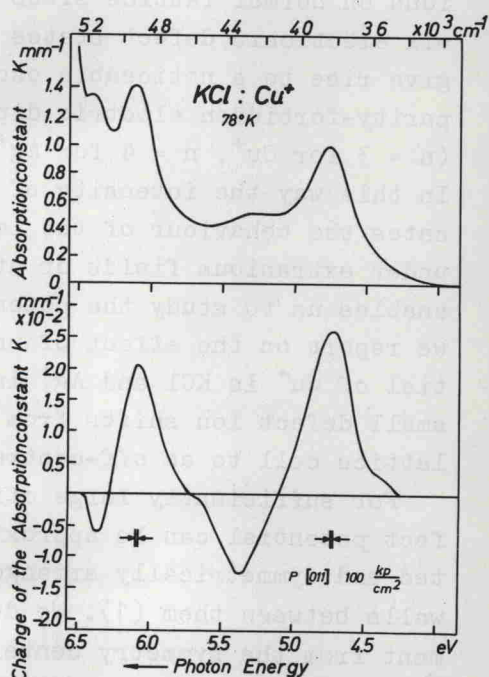


Fig.1. Difference of absorption constant of  $\text{KCl}:\text{Cu}^+$  for light polarized parallel and perpendicular to the stress axis.